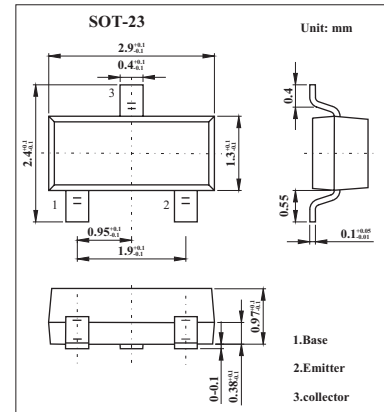


## Silicon PNP Epitaxial

## 2SA1566

## ■ Features

- Low frequency amplifier.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector to base voltage	$V_{CB0}$	-120	V
Collector to emitter voltage	$V_{CE0}$	-120	V
Emitter to base voltage	$V_{EB0}$	-5	V
Collector current	$I_C$	-100	mA
Collector power dissipation	$P_C$	150	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{(BR)CB0}$	$I_C = -10 \mu\text{A}, I_E = 0$	-120			V
Collector to emitter breakdown voltage	$V_{(BR)CE0}$	$I_C = -1 \text{ mA}, R_{BE} = \infty$	-120			V
Emitter to base breakdown voltage	$V_{(BR)EB0}$	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Collector cutoff current	$I_{CBO}$	$V_{CB} = -70 \text{ V}, I_E = 0$			-0.1	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -2 \text{ V}, I_C = 0$			-0.1	$\mu\text{A}$
DC current transfer ratio	$h_{FE}$	$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$	250		800	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$			-0.15	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$			1.2	V

■  $h_{FE}$  Classification

Marking	JID	JIE
Rank	D	E
$h_{FE}$	250~500	400~800